ECH8690

Power MOSFET 60V, 4.7A, 55mΩ -60V, -3.5A, 94mΩ Complementary Dual ECH8

Features

- On-State Resistance Nch:RDS(on)1=42mΩ(typ.) Pch:RDS(on)1=73mΩ(typ.)
- 4V drive
- Nch+Pch MOSFET

- COR ON Semiconductor® http://onsemi.com
- Protection diode in
- Halogen free compliance

Specifications

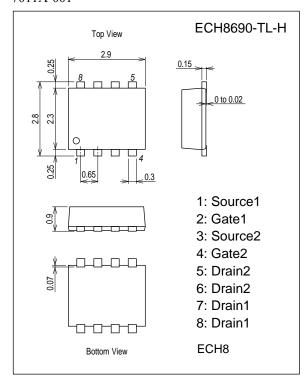
Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	N-channel P-channel		Unit
Drain to Source Voltage	V _{DSS}		60	V	
Gate to Source Voltage	VGSS		±20	±20	V
Drain Current (DC)	۱ _D		4.7	-3.5	А
Drain Current (Pulse)	I _{DP}	PW≤10µs, duty cycle≤1%	30	-30	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)1unit		W	
Total Dissipation	PT	When mounted on ceramic substrate (1200mm ² ×0.8mm)		W	
Channel Temperature	Tch			°C	
Storage Temperature	Tstg			°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

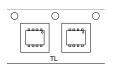
unit : mm (typ) 7011A-001



Ordering & Package Information

•	U		
Device	Package	Shipping	note
ECH8690-TL-H	ECH8	3000 pcs. / reel	Pb-Free and Halogen Free

Packing Type: TL



Electrical Connection

Marking



LOT No.

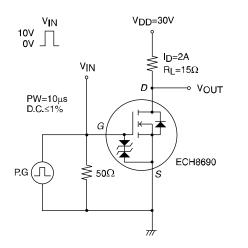
ECH8690

Electrical Characteristics at $Ta = 25^{\circ}C$

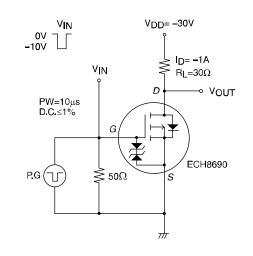
Parameter	Symbol	Conditions		Ratings		
Falanielei	Symbol	Conditions	min	typ	max	Unit
[N-channel]						-
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	IGSS	$V_{GS}=\pm 16V, V_{DS}=0V$			±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A		4.2		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =2A, V _{GS} =10V		42	55	mΩ
	R _{DS} (on)2	I _D =1A, V _{GS} =4.5V		53	74	mΩ
	R _{DS} (on)3	I _D =1A, V _{GS} =4V		61	85	mΩ
Input Capacitance	Ciss			955		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		58		pF
Reverse Transfer Capacitance	Crss			45		pF
Turn-ON Delay Time	t _d (on)			7		ns
Rise Time	tr	See specified Test Circuit.		8.4		ns
Turn-OFF Delay Time	t _d (off)			76		ns
Fall Time	tf			23		ns
Total Gate Charge	Qg			18		nC
Gate to Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =4.7A		3		nC
Gate to Drain "Miller" Charge	Qgd			2.8		nC
Diode Forward Voltage	V _{SD}	IS=4.7A, VGS=0V		0.82	1.2	V
[P-channel]						
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V			-1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-1.5A		3.4		S
	R _{DS} (on)1	I _D =-1A, V _{GS} =-10V		73	94	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-0.5A, V _{GS} =-4.5V		97	135	mΩ
	R _{DS} (on)3	I _D =-0.5A, V _{GS} =-4V		108	153	mΩ
Input Capacitance	Ciss			790		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		63		pF
Reverse Transfer Capacitance	Crss			45		pF
Turn-ON Delay Time	t _d (on)			10		ns
Rise Time	tr	See specified Test Circuit.		8.8		ns
Turn-OFF Delay Time	t _d (off)			84		ns
Fall Time	tf			29		ns
Total Gate Charge	Qg			15		nC
Gate to Source Charge	Qgs	V _{DS} =-30V, V _{GS} =-10V, I _D =-3.5A		2.6		nC
Gate to Drain "Miller" Charge	Qgd	7		2.2		nC
Diode Forward Voltage	VSD	IS=-3.5A, VGS=0V		-0.83	-1.2	V

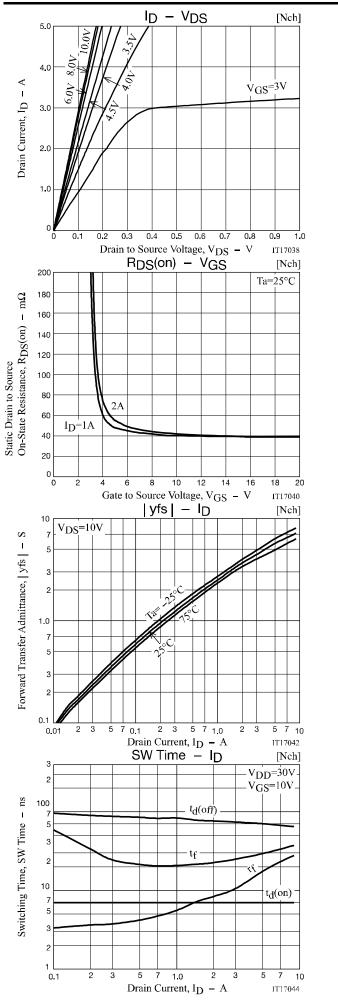
Switching Time Test Circuit

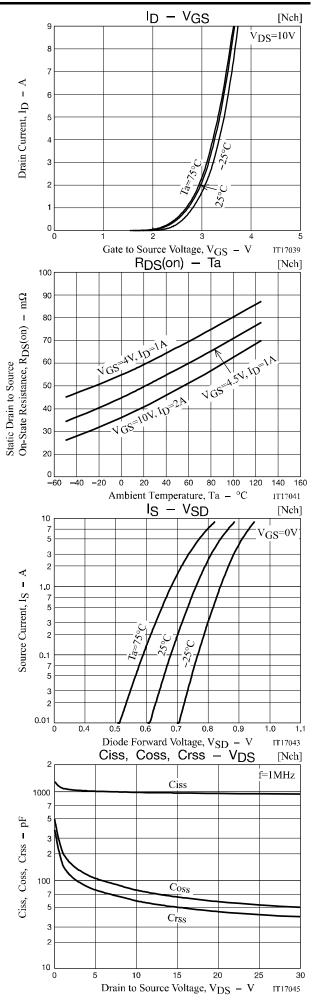
[N-channel]



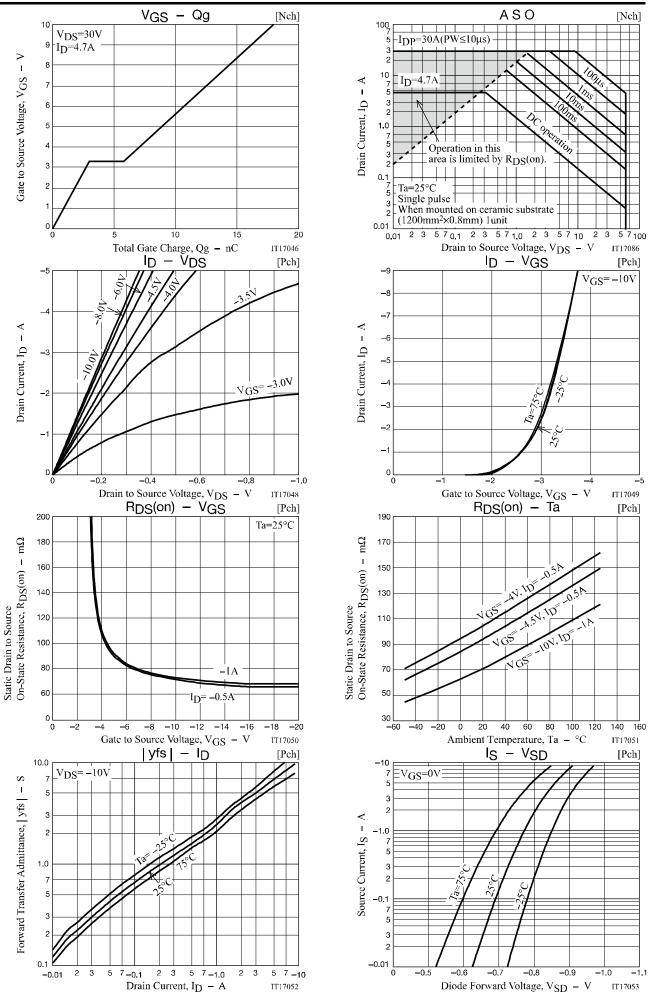
[P-channel]

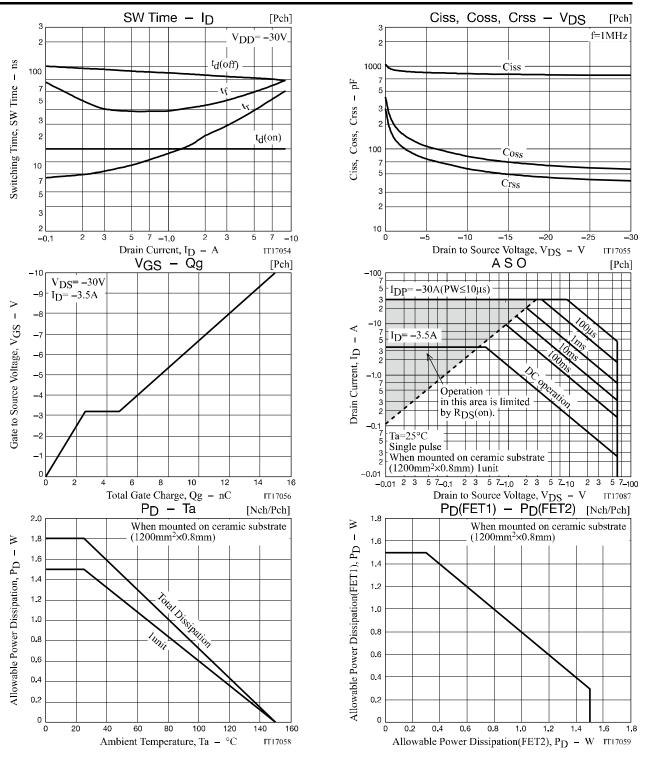






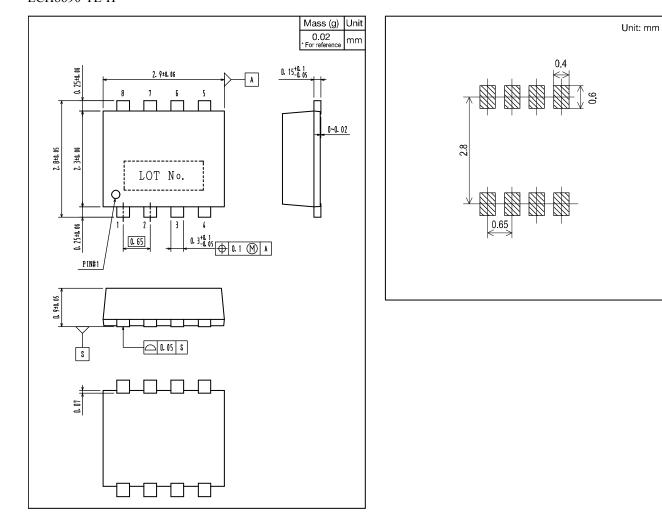
ECH8690





Outline Drawing ECH8690-TL-H





Note on usage : Since the ECH8690 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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